

impurity having a first conductivity into the semiconductor layer; forming source and drain electrodes, the source and drain electrodes directly contacting both end portions of the semiconductor layer; ion-implanting an impurity having a second conductivity into the semiconductor layer to form high-density source and drain regions and a channel area, the high-density source and drain regions directly contacting the source and drain electrodes; forming a
5 first insulating layer over the entire surface of the insulating substrate; forming a pixel electrode having an opening portion formed thereon; and forming a gate electrode on a portion of the first insulating layer over the semiconductor layer.

The method further includes forming a contact hole contemporaneously with forming the
10 pixel electrode having the opening portion, the contact hole contacting the first capacitor electrode and the gate electrode.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the present invention and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying
15 drawings, in which like reference numerals denote like parts, and in which:

FIG. 1 is a cross-sectional view illustrating a conventional organic EL display device;

FIG. 2 is a plan view illustrating an embodiment of an organic EL display device according to the present invention;

FIGs. 3A to 3H are cross-sectional views taken along line III-III of FIG. 2;

20 FIG. 4 is a cross-sectional view taken along line IV-IV of FIG. 2; and

FIG. 5 is a cross-sectional view illustrating another embodiment of the organic EL display device according to the present invention.